METHOD OF PASSIVATING SEMICONDUCTOR DEVICE

Abstract

The invention relates to a method of passivating a semiconductor device with two types of transistors, e.g., NMOS and PMOS transistors. The semiconductor device is placed in a pressurized sealed chamber and at least two different passivating gases are introduced into the chamber. Since the two passivating gases can be selected to have one gas suitable for passivating PMOS transistors and the other gas suitable for NMOS transistors, the method of the present invention can achieve a better result for both the NMOS and PMOS transistors.